



AC857BQ-AC857CQ

PNP SMALL SIGNAL TRANSISTOR IN SOT23

Description

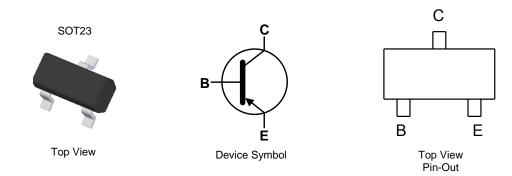
The AC857BQ-AC857CQ Bipolar Junction Transistors (BJT) are designed to meet the stringent requirements of Automotive Applications.

Features

- Ideally Suited for Automatic Insertion
- Complementary NPN Types: AC847BQ-AC847CQ
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.008 grams (Approximate)



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Quantity per Reel
AC857BQ-7	Automotive	2C6	7	3,000
AC857CQ-7	Automotive	2C7	7	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

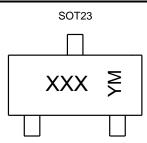
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



XXX = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2016	20	017	2018	2	019	2020		2021	2022		2023
Code	D		E	F		G	Н			J		K
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	•••••		inai		may	oun	• • • •				-	



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Continuous Collector Current	lc	-100	mA
Peak Collector Current	Ісм	-200	mA
Peak Emitter Current	I _{EM}	-200	mA
Peak Base Current	I _{BM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P	310	mW
	(Note 7)	- P _D	350	TTIVV
Thermal Basistones, Junction to Ambient	(Note 6)	D	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	357	0/00
Thermal Resistance, Junction to Leads (Note 8)		R _{0JL}	350	°C/W
Operating and Storage Temperature Range	T _J ,T _{STG}	-65 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

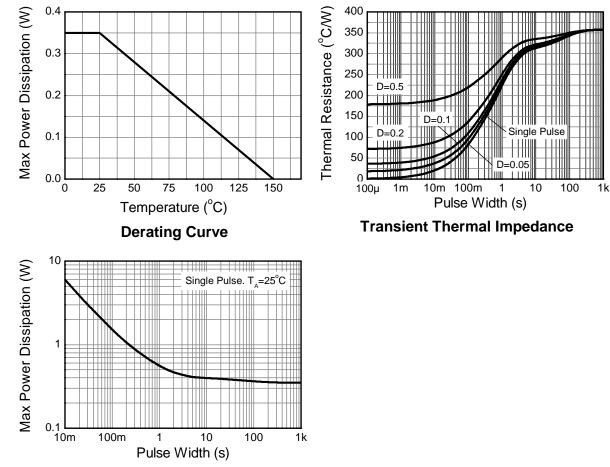
Notes: 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

7. Same as Note 6, except the device is mounted on 15mm x 15mm 1oz copper.

Barrow Comparison of the device is mounted of romma forming to any 102 control of the leads).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



Pulse Power Dissipation



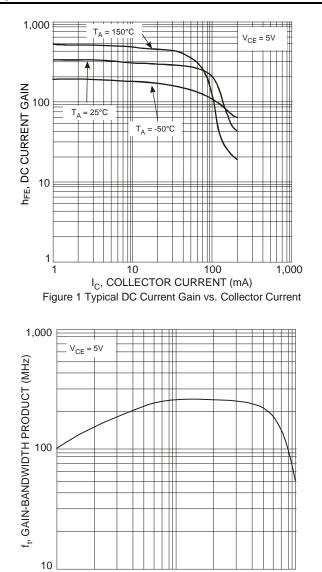
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

				-			
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	-50	—		V	I _C = -10μΑ
Collector-Emitter Breakdown Voltage (Note 10))	BV _{CEO}	-45	—	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage		BV _{EBO}	-5	—		V	$I_E = -1\mu A$
Collector Cutoff Current			1		-15	nA	V _{CB} = -30V
		I _{CBO}			-4	μA	V _{CB} = -30V, T _J = +150°C
Collector Emitter Cutoff Current		I _{CES}		_	-15	nA	V _{CE} = -50V
Emitter-Base Cutoff Current		I _{EBO}		_	-100	nA	V _{EB} = -5V
AC857E		_	_	330	_		
Small Signal Current Gain (Note 10)	AC857CQ	h _{fe}	_	600			
Input Impedance (Note 10)	AC857BQ	h	_	4.5	_	kΩ	$I_{C} = -2.0$ mA, $V_{CE} = -5V$ f = 1.0kHz
input impedance (Note 10)	AC857CQ	h _{ie}	—	8.7			
Output Admittance (Note 10)	AC857BQ	h _{oe}	_	30	—	μS	
	AC857CQ	lioe	—	60	—		
Reverse Voltage Transfer Ratio (Note 10)	AC857BQ	h _{re}		2x10 ⁻⁴	_	—	
	AC857CQ		—	3x10⁻⁴	—		l
DC Current Gain (Note 10)	AC857BQ	h _{FE}	hee 220 290 475		$I_{\rm C} = -2.0 \text{mA}, V_{\rm CE} = -5 \text{V}$		
	AC857CQ		420	520	800		
Collector-Emitter Saturation Voltage (Note 10)		V _{CE(SAT)}		-75	-300	mV	$I_{\rm C}$ = - 10mA, $I_{\rm B}$ = -0.5mA
		VCE(SAT)		-250	-650		$I_{\rm C}$ = - 100mA, $I_{\rm B}$ = -5.0mA
Base-Emitter Turn-On Voltage (Note 10)		M	-600	-650	-750	mV	$I_{C} = -2mA, V_{CE} = -5V$
Dase-Emilier rum-On voltage (Note 10)		V _{BE(ON)}	—	—	-820	IIIV	$I_{C} = -10mA, V_{CE} = -5V$
Base Emitter Seturation Voltage (Note 10)				-700	_	mV	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = -0.5 {\rm mA}$
Base-Emitter Saturation Voltage (Note 10)		V _{BE(SAT)}	_	-850	-1100	IIIV	I _C = -100mA, I _B = -5mA
Output Capacitance		C _{obo}		3		pF	V _{CB} = -10V, f = 1.0MHz
Transition Frequency		f _T	100	200	—	MHz	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$
Noise Figure		NF	_	2	10	dB	$\label{eq:VCE} \begin{array}{l} V_{CE} = \text{-}5V, \ I_{C} = \text{-}200\muA\\ R_{S} = 2k\Omega, \ f = 1kHz\\ \Deltaf = 200Hz \end{array}$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



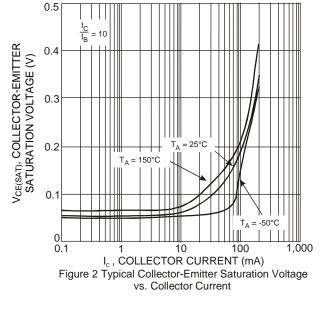
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



 1
 10
 100

 I_c, COLLECTOR CURRENT (mA)
 100
 100

 Figure 3 Gain-Bandwidth Product vs Collector Current
 100
 100

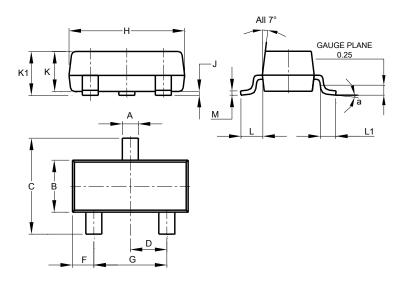




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

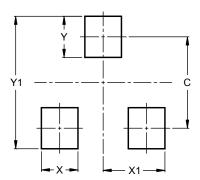
SOT23



	SO	T23	
Dim	Min	Max	Тур
Α	0.37	0.51	0.40
в	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
н	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
Μ	0.085	0.150	0.110
а	0°	8°	
All	Dimens	ions in	mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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